

#### **80V NPN DARLINGTON TRANSISTOR IN SOT223**

#### **Features**

- BVcEo > 80V
- BVcBo > 100V
- Ic = 2A High Continuous Current
- Useful hFE up to 6A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
  - https://www.diodes.com/quality/product-definitions/
- An automotive-compliant part is available under separate datasheet (FZT603Q)

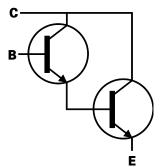
### **Mechanical Data**

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound;
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

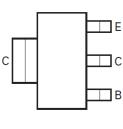




Top View







Top View Pinout

### **Ordering Information** (Note 4)

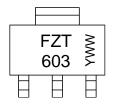
Orderable Part Number	Package	Marking	Reel Size (inches)	Tono Width (mm)	Packing	
				Tape Width (mm)	Qty.	Carrier
FZT603TA	SOT223 (Type DN)	FZT603	7	12	1,000	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

SOT223 (Type DN)



$$\label{eq:FZT603} \begin{split} & \text{FZT603} = \text{Product Type Marking Code} \\ & \text{YWW} = \text{Date Code Marking} \\ & \text{Y or } \overline{\text{Y}} = \text{Last Digit of Year (ex: 5 = 2025)} \\ & \text{WW or } \overline{\text{WW}} = \text{Week Code (01 to 53)} \end{split}$$



# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	100	V
Collector-Emitter Voltage	VCEO	80	V
Emitter-Base Voltage	VEBO	10	V
Continuous Collector Current	Ic	2	Α
Peak Pulse Current	Ісм	6	Α

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		3.0		
Dower Dissipation	(Note 6)	D-	2.0	W	
Power Dissipation	(Note 7)	PD	1.6		
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Desigtance Investigants Ambient	(Note 6)	D- · ·	62.5	ı	
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>0</sub> JA	78.1		
	(Note 8)		104	°C/W	
Thermal Resistance, Junction to Lead (Note 9)		Rejl	12.9		
Thermal Resistance, Junction to Case	(Note 6)	D	1.1	1	
Thermal Resistance, Junction to Case	(Note 7)	Rejc	4.7		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

## ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.

  9. Thermal resistance from junction to solder-point (at the end of the collector lead).

  10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### Thermal Characteristics and Derating Information

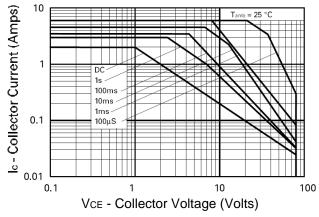


Figure 1. Safe Operating Area

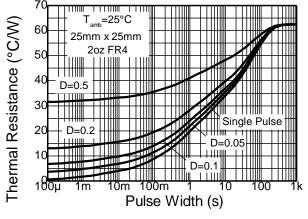


Figure 2. Transient Thermal Impedance

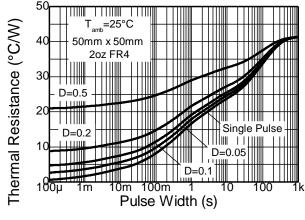


Figure 3. Transient Thermal Impedance

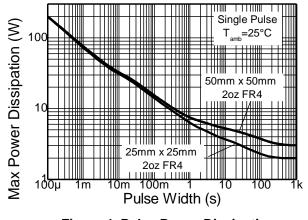


Figure 4. Pulse Power Dissipation

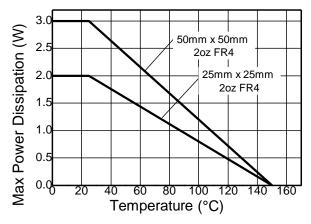


Figure 5. Derating Curve



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	ВУсво	100	240	_	V	Ic = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BVceo	80	110	-	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BVEBO	10	16	_	V	I <sub>E</sub> = 100μA
Collector-Base Cutoff Current	Ісво	_	_	10 10	nΑ μΑ	V <sub>CB</sub> = 80V V <sub>CB</sub> = 80V, T <sub>A</sub> = +100°C
Collector-Emitter Cutoff Current	I <sub>CES</sub>	_	_	10	μΑ	V <sub>CES</sub> = 80V
Emitter Cutoff Current	IEBO	_	_	100	nA	V <sub>EB</sub> = 8V
DC Current Gain (Note 11)	hFE	3,000 5,000 3,000 2,000 —	14,000 15,000 14,000 10,000 2,000 750	100,000 — — — —	ı	Ic = 50mA, VcE = 5V Ic = 500mA, VcE = 5V Ic = 1A, VcE = 5V Ic = 2A, VcE = 5V Ic = 5A, VcE = 5V Ic = 6A, VcE = 5V
Collector-Emitter Saturation Voltage (Note 11)	VCE(sat)	1111	0.79 0.80 0.88 0.99 0.86	0.88 0.90 1.00 1.13	V	Ic = 250mA, I <sub>B</sub> = 0.25mA Ic = 0.4A, I <sub>B</sub> = 0.4mA Ic = 1A, I <sub>B</sub> = 1mA Ic = 2A, I <sub>B</sub> = 20mA Ic = 2A, I <sub>B</sub> = 20mA, T <sub>J</sub> = +150°C
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	_	1.70	1.95	V	Ic = 2A, I <sub>B</sub> = 20mA
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	_	1.50	1.75	V	Ic = 2A, VcE = 5V
Input Capacitance (Note 11)	C <sub>ibo</sub>	_	90	_	pF	V <sub>EB</sub> = 0.5V, f = 1MHz
Output Capacitance (Note 11)	Cobo	_	15	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Current Gain-Bandwidth Product (Note 11)	f⊤	150	_	_	MHz	$V_{CE} = 10V, I_{C} = 100mA$ f = 20MHz
Turn-On Time	ton	_	0.5	_	μs	V <sub>CC</sub> = 10V, I <sub>C</sub> = 500mA
Turn-Off Time	t <sub>off</sub>	_	1.6	_	μs	$I_{B1} = -I_{B2} = 0.5 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

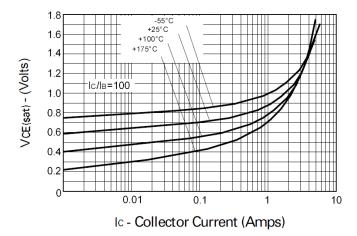


Figure 6. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

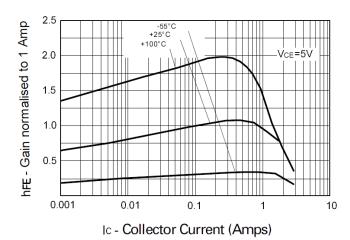


Figure 7. h<sub>FE</sub> vs. I<sub>C</sub>

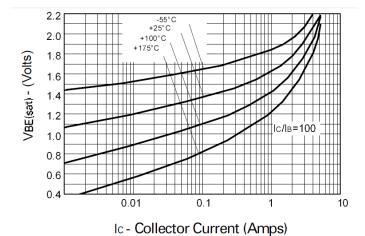
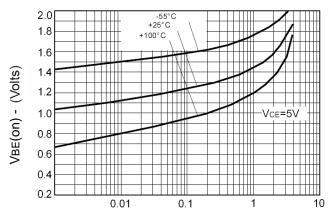


Figure 8. V<sub>BE(sat)</sub> vs. I<sub>C</sub>



Ic - Collector Current (Amps)

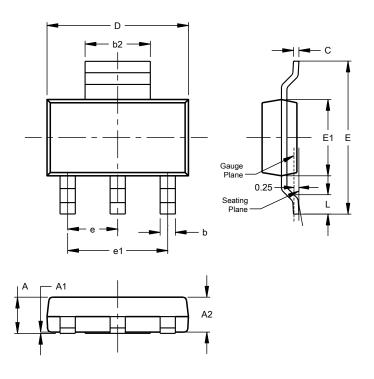
Figure 9. V<sub>BE(on)</sub> vs. I<sub>C</sub>



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

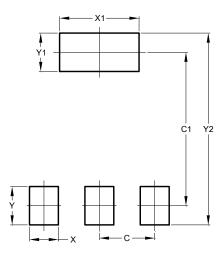


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10	-		
С	0.20	0.32	-		
D	6.30	6.70			
Е	6.70	7.30	-		
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
V2	8 00



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